



30V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
30V	$5.5 \text{m}\Omega$ @ $V_{GS} = 10V$	75A
307	$8.5 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	50A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

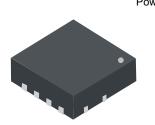
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

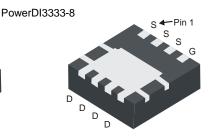
Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (Test in Production) Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Excellent Q_{qd x} R_{DS(ON)} Product (FOM)
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% UIS (Avalanche) Rated
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note4)

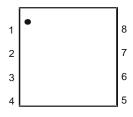
Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)

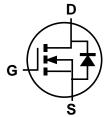




Top View Bottom View







Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH3004LFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMTH3004LFGQ-13	PowerDI3333-8	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



YS5 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±16	V	
Continuous Drain Current (Notes 7 & 10) V _{GS} = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	75 52	А
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$		I _D	15 10	А
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	3	А	
Pulsed Drain Current (100µs Pulse, Duty Cycle = 1%)	I _{DM}	250	А	
Pulsed Body Diode Forward Current (100µs Pulse, Duty Cyc	I _{SM}	250	А	
Avalanche Current, L=0.3mH	I _{AS}	27	Α	
Avalanche Energy, L=0.3mH	E _{AS}	110	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 7)	$T_C = +25^{\circ}C$	P_{D}	50	W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	3	°C/W	
Total Power Dissipation (Note 6) $T_A = +25^{\circ}C$		P_{D}	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{ heta JA}$	60	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +175	°C

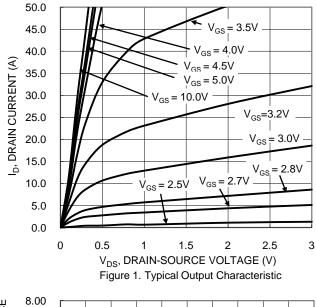
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	1 - 7	1	71				
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		-	4.1	5.5	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Diani-Source On-Resistance	R _{DS(ON)}	-	6.2	8.5		$V_{GS} = 4.5V, I_{D} = 7A$	
Diode Forward Voltage	V_{SD}	=	0.7	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	-	2370	-		V _{DS} = 15V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	-	1360	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	240	-			
Gate Resistance	Rg	=	0.6	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	-	20	-	_		
Total Gate Charge (V _{GS} = 10V)	Qg	-	44	-			
Gate-Source Charge	Q_{gs}	-	7	-	IIC	$V_{DS} = 15V, I_D = 20A$	
Gate-Drain Charge	Q_{gd}	-	8	-			
Turn-On Delay Time	t _{D(ON)}	-	6.2	-			
Turn-On Rise Time	t _R	-	4.3	-		$V_{DD} = 15V, V_{GS} = 10V,$ $R_L = 0.75\Omega, R_g = 3\Omega, I_D = 20A$	
Turn-Off Delay Time	t _{D(OFF)}	-	21	-	ns		
Turn-Off Fall Time	t _F	-	8	-			
Body Diode Reverse Recovery Time	t _{RR}	-	25	-	ns	1 454 11/11 5004/	
Body Diode Reverse Recovery Charge	Q_{RR}	=	37	-	nC	I _F = 15A, di/dt = 500A/μs	

- 6. R_{0JA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. R_{0JC} is guaranteed by design while R_{0JA} is determined by the user's board design.

 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.
- 10. Package limited.





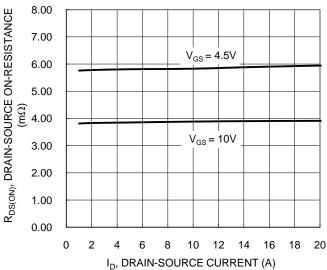


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

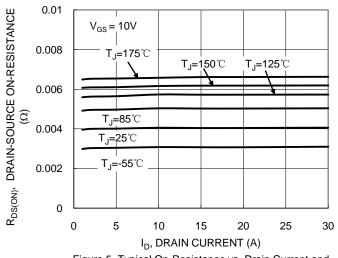


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

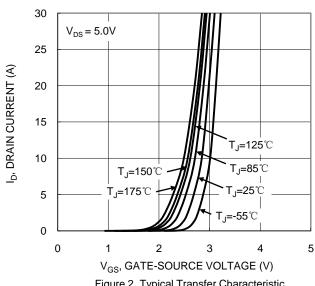


Figure 2. Typical Transfer Characteristic

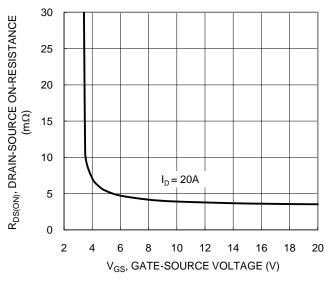


Figure 4. Typical Transfer Characteristic

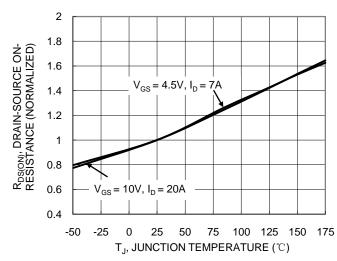


Figure 6. On-Resistance Variation with Temperature



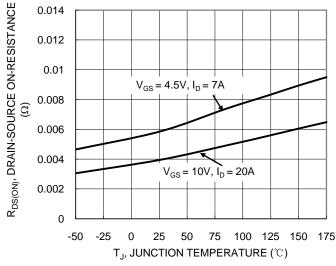


Figure 7. On-Resistance Variation with Temperature

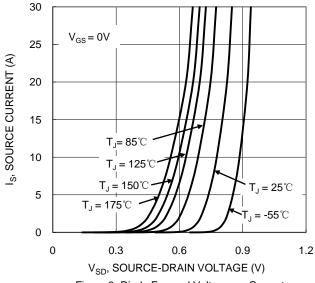


Figure 9. Diode Forward Voltage vs. Current

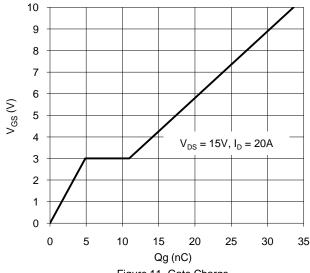


Figure 11. Gate Charge

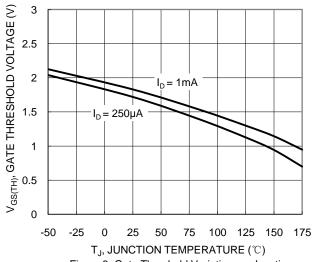
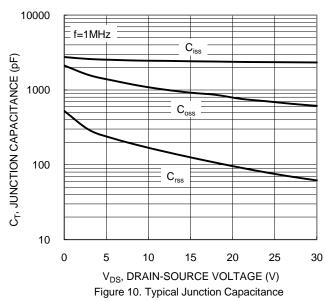


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R_{DS(ON)} Limited $P_W = 10 \mu s$ 100 ID, DRAIN CURRENT (A) 10 $P_{vv} = 100 \mu s$ 1 $P_W = 1 \text{ms}$ $T_{J(Max)} = 175^{\circ}C$ $T_C = 25^{\circ}C$ 0.1 P_W =100ms Single Pulse **DUT** on Infinite Heatsink $P_W = 1s$ V_{GS}= 10V 0.01 0.01 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



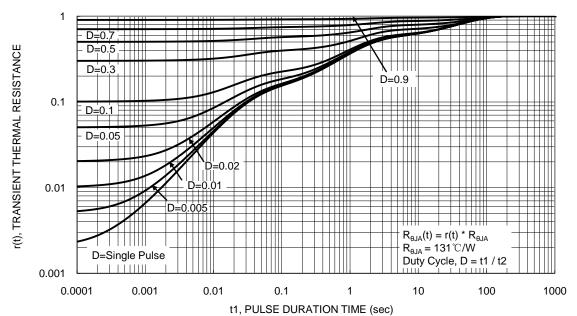


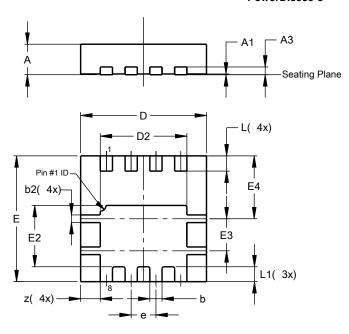
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

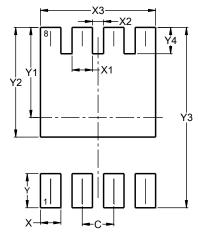


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	-	-	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	_	_	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	-	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2018, Diodes Incorporated

www.diodes.com